

SxX8BBSx Series

EV Series 0.8 Amp Sensitive SCRs

HF RoHS



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	200 to 450	μA

Description

This new sensitive SCR component series offers 600V V_{DRM} and 0.8A $I_{T(RMS)}$ capability in the smallest package size in the industry, SOT23. It is specifically designed for GFCI (Ground Fault Circuit Interrupter) applications. All SCRs junctions are glass-passivated to ensure long term reliability and parametric stability.

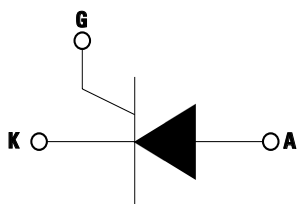
Features

- Very compact SOT23 SMT package
- Surge current capability up to 12A @ 60Hz
- Blocking voltage (V_{DRM}/V_{RRM}) capability - up to 600V
- High dv/dt noise immunity
- Improved turn-off time (t_q) < 25 μsec
- Sensitive gate for direct microprocessor interface
- RoHS compliant and Halogen-Free

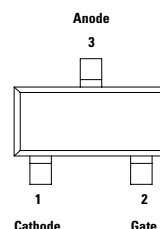
Applications

The SxX8BBS series is specifically designed for GFCI (Ground Fault Circuit Interrupter) and applications.

Schematic Symbol



Pin out



Absolute Maximum Ratings

Symbol	Parameter			Value	Unit
V_{DSM}/V_{RSM}	Peak non-repetitive blocking voltage	Pw=100 μs		700	V
$I_{T(RMS)}$	RMS on-state current (full sine wave)		$T_c = 80^\circ C$	0.8	A
$I_{T(AV)}$	Average on-state current		$T_c = 80^\circ C$	0.51	A
I_{TSM}	Non repetitive surge peak on-state current (Single cycle, T_j initial = 25 $^\circ C$)		f= 50Hz	10	A
			f= 60Hz	12	A
I^2t	I^2t Value for fusing	$t_p = 10$ ms	f= 50 Hz	0.5	A ² s
		$t_p = 8.3$ ms	f= 60 Hz	0.6	A ² s
di/dt	Critical rate of rise of on-state current $I_G = 10mA$	60 Hz	$T_j = 125^\circ C$	80	A/ μs
I_{GM}	Peak Gate Current	$t_p = 20 \mu s$	$T_j = 125^\circ C$	1.0	A
$P_{G(AV)}$	Average gate power dissipation	—	$T_j = 125^\circ C$	0.1	W
T_{stg}	Storage junction temperature range	—	—	-40 to 150	$^\circ C$
T_j	Operating junction temperature range	—	—	-40 to 125	$^\circ C$

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Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value		Unit
				SxX8BBS	SxX8BBS3	
I _{GT}	DC Gate Trigger Current	V _D = 6V, R _L = 100 Ω	MIN.	50	70	μA
			TYP.	70	200	
			MAX.	200	450	
V _{GT}	DC Gate Trigger Voltage	V _D = 6V, R _L = 100 Ω	MAX.	0.8		V
V _{GRM}	Peak Reverse Gate Voltage	I _{RG} = 10μA	MIN.	8		V
I _H	Holding Current	Initial Current = 20mA	MAX.	10		mA
			TYP.	5		
(dv/dt)s	Critical Rate-of-Rise of Off-State Voltage	T _J = 125°C V _D = 67% V _{DRM} / V _{RRM} Exp. Waveform, R _{GK} =1 kΩ	MIN.	50	350	V/μs
V _{GD}	Gate Non-Trigger Voltage	V _D = V _{DRM} , R _{GK} =1 kΩ T _J = 125°C	MIN.	0.2		V
t _q	Turn-Off Time	I _T = 0.5A	MAX.	25	20	μs
t _{gt}	Turn-On Time	I _G = 10mA, Pw = 15μsec, I _T = 1.6A(pk)	TYP.	2.0		μs

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
V_{TM}	Peak On-State Voltage	$I_{TM} = 1.6\text{A (pk)}$	MAX.	1.70	V
I_{DRM} / I_{RRM}	V_{DRM} / V_{RRM}	$T_J = 25^\circ\text{C}$	MAX.	5	μA
		$T_J = 125^\circ\text{C}$	MAX.	100	μA

Thermal Resistances

Symbol	Description	Value	Unit
$R_{\theta(JC)}$	Junction to case (AC)	45	$^\circ\text{C/W}$
$R_{\theta(JA)}$	Junction to ambient	220	$^\circ\text{C/W}$

Figure 1:
Normalized DC Gate Trigger Current vs.
Junction Temperature

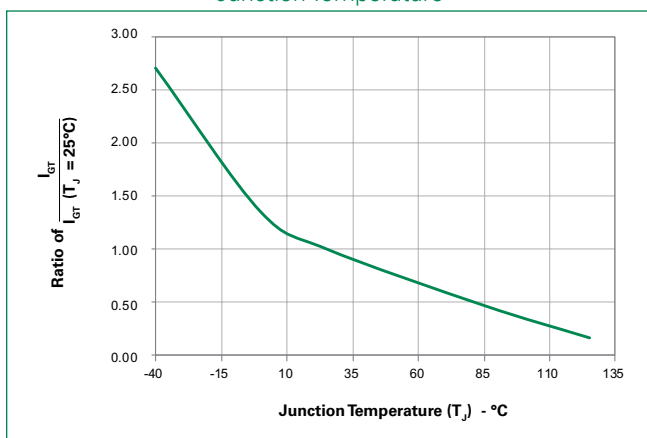
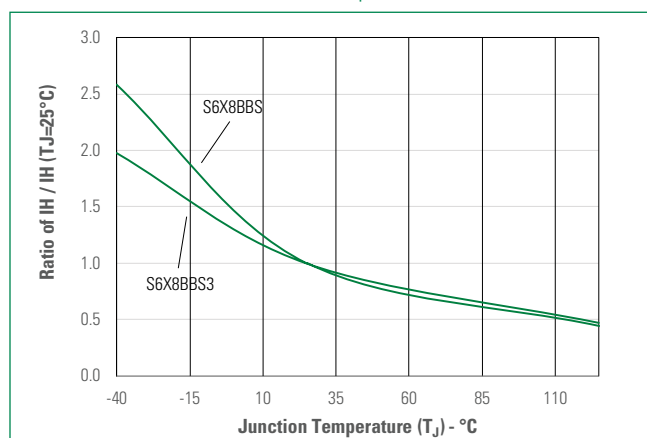


Figure 2:
Normalized DC Holding Current vs.
Junction Temperature

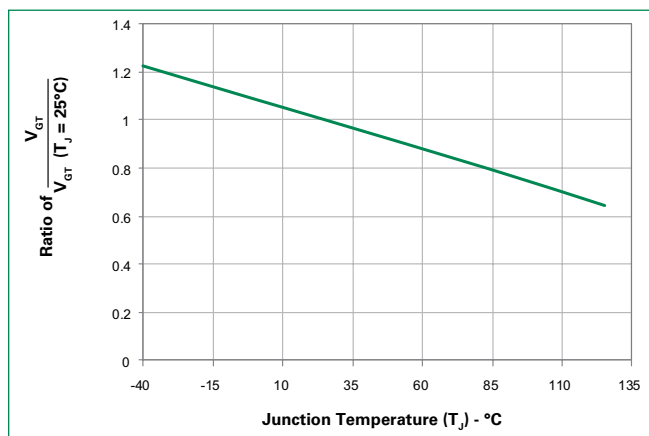


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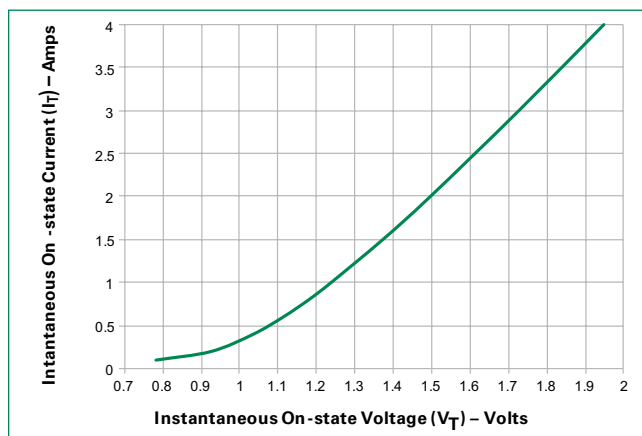
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Figure 3:

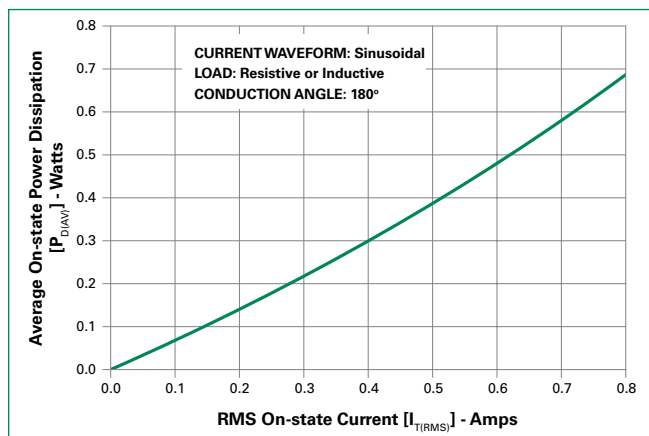
Normalized DC Gate Trigger Voltage vs. Junction Temperature

**Figure 4:**

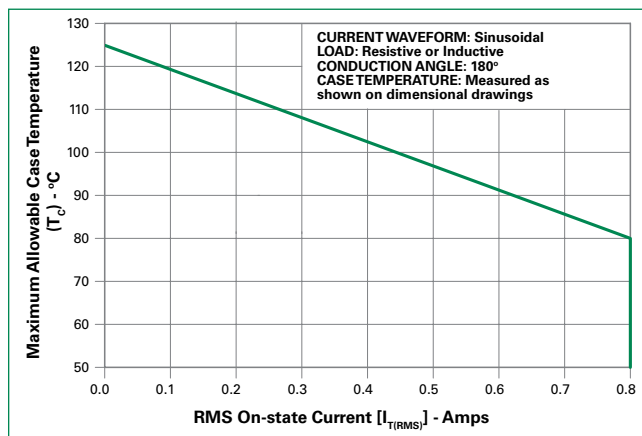
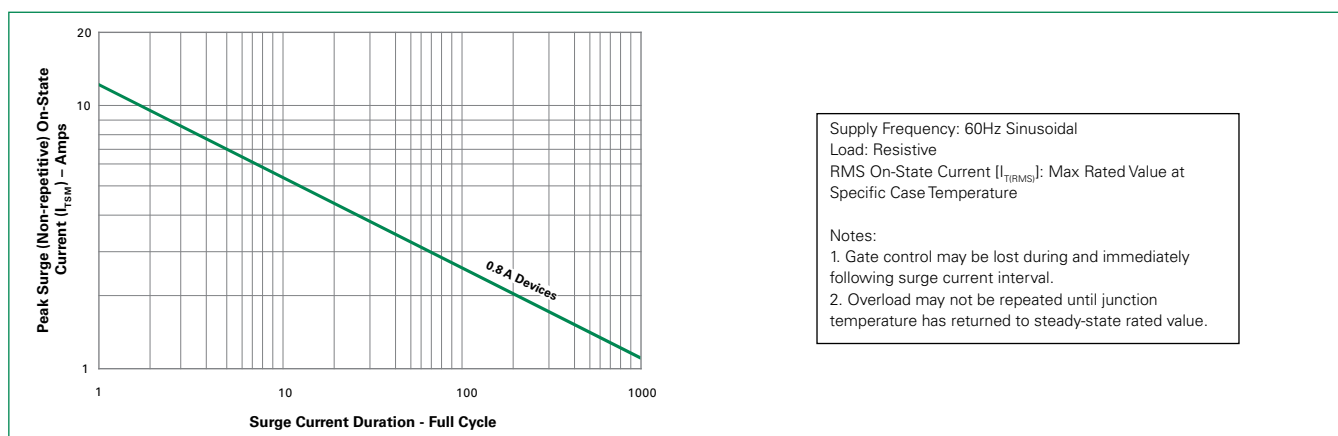
On-State Current vs. On-State Voltage (Typical)

**Figure 5:**

Power Dissipation (Typical) vs. RMS On-State Current

**Figure 6:**

Maximum Allowable Case Temperature vs. On-State Current

**Figure 7:** Surge Peak On-State Current vs. Number of Cycles

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Figure 8:

Static dv/dt vs. RGK vs. Junction Temperature (S6X8BBS)

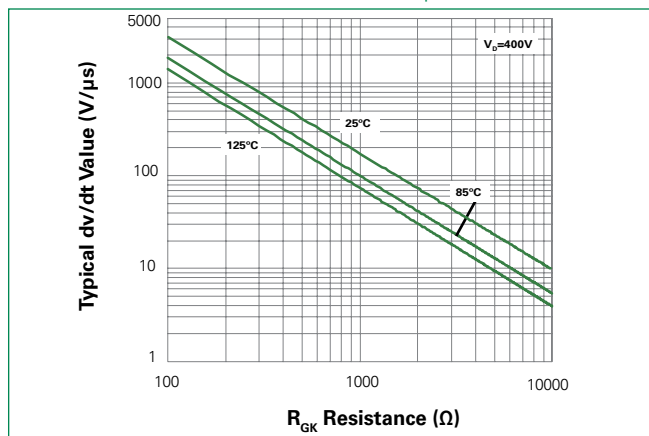


Figure 9:

Static dv/dt vs. CGK vs. Junction Temperature (S6X8BBS)

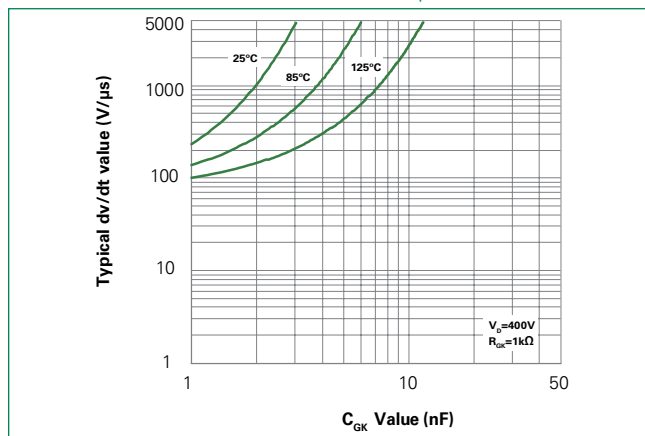


Figure 10:

Static dv/dt vs. RGK vs. Junction Temperature (S6X8BBS3)

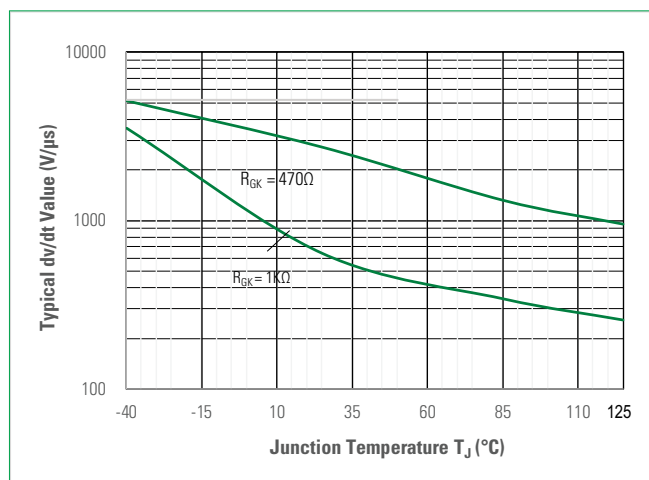
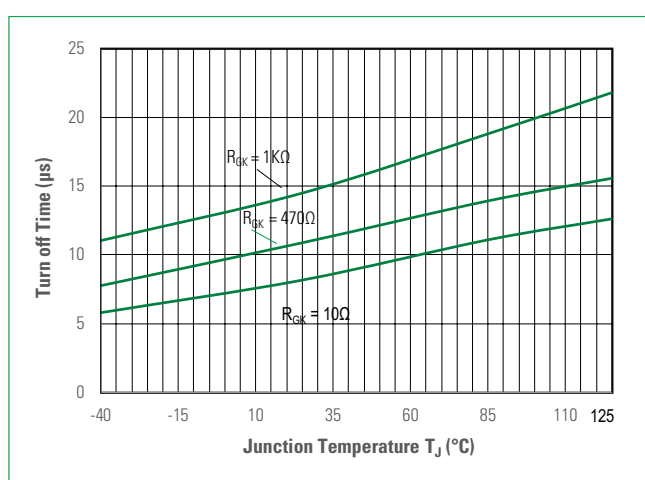


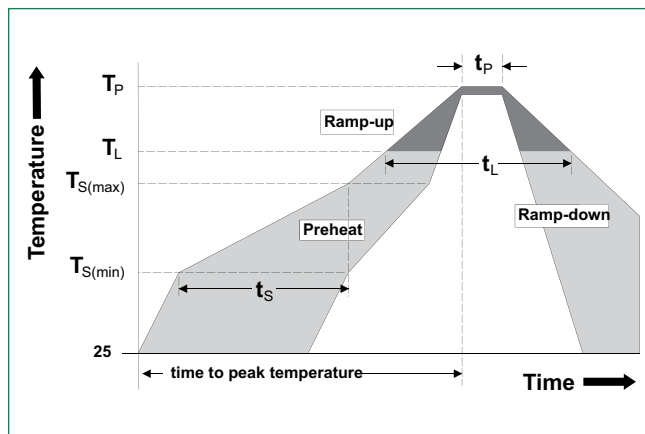
Figure 11:

Static dv/dt vs. CGK vs. Junction Temperature (S6X8BBS3)



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 120 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		30 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



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Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL Recognized compound meeting flammability rating V-0.
Lead Material	Copper Alloy

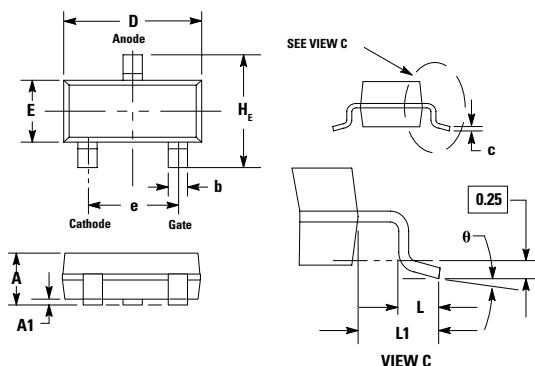
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

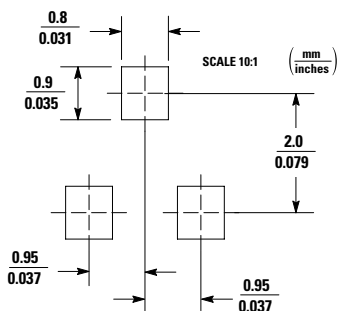
Reliability/Environmental Tests

Test	Specifications and Conditions
HTRB (AC Blocking)	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ V_{DRM} @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -55°C to +150°C; 15-min dwell-time
H3TRB	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
UHASt	ESD22-A118, 96hours, 130°C, 85%RH
Resistance to Solder Heat	MIL-STD-750 Method 2031, 260°C, 10s
Solderability	ANSI/J-STD-002, category 3, Test A
Moisture Sensitivity Level	Level 1, JEDEC-J-STD-020D

Dimensions – SOT-23



SOLDERING FOOTPRINT



Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.04	0.04	0.04	0.89	1.02	1.12
A1	0.00	0.00	0.01	0.01	0.10	0.15
b	0.02	0.02	0.02	0.38	0.46	0.51
c	0.00	0.01	0.01	0.08	0.13	0.18
D	0.11	0.11	0.12	2.80	2.90	3.04
E	0.05	0.05	0.06	1.19	1.30	1.40
e	0.07	0.08	0.08	1.78	1.91	2.06
L	0.02	0.02	0.02	0.40	0.49	0.60
L1	0.01	0.02	0.03	0.36	0.53	0.74
H	0.08	0.09	0.10	2.10	2.30	2.64
Θ	0°	-	10°	0°	-	10°

Product Selector

Part Number	Voltage 600V	Gate Sensitivity	Package
S6X8BBS	X	200 μ A	SOT-23
S6X8BBS3	X	450 μ A	SOT-23

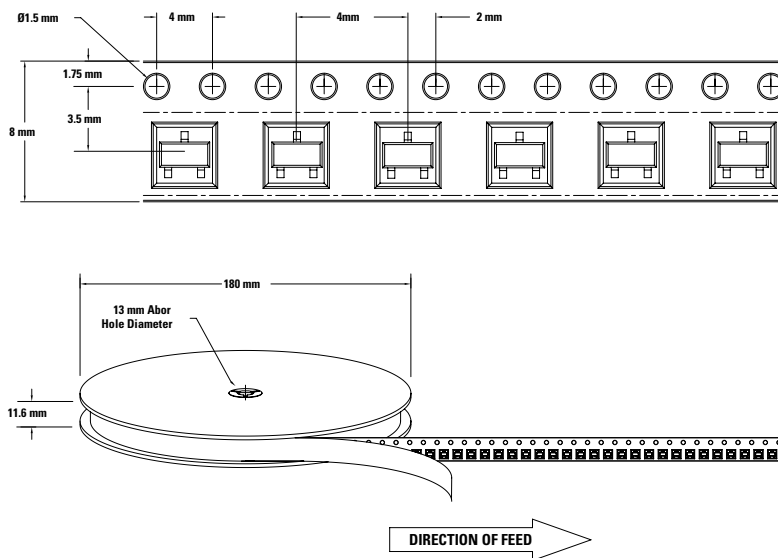
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
S6X8BBSRP	6X8	0.01g	Tape & Reel	3000
S6X8BBS3RP	6X83	0.01g	Tape & Reel	3000

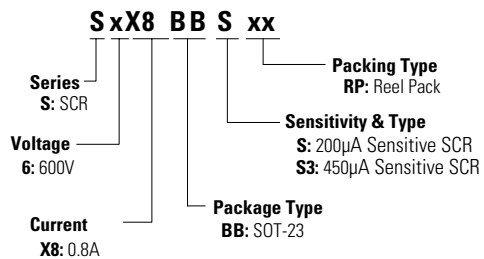
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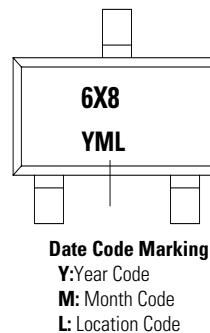
SOT-23 Reel Pack (RP) Specifications



Part Numbering System



Part Marking System



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